TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

# SM12G45,SM12J45,SM12G45A,SM12J45A

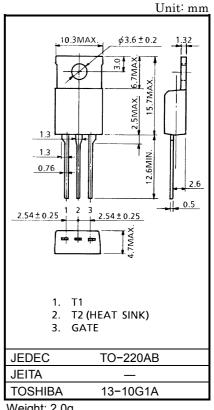
### AC POWER CONTROL APPLICATIONS

• R.M.S On-State Current  $: I_{T (RMS)} = 12A$ 

• High Commutating (dv / dt)

### **MAXIMUM RATINGS**

CHARACTERIS	SYMBOL	RATING	UNIT		
Repetitive Peak Off-State Voltage	SM12G45 SM12G45A	Vanu	400	V	
	SM12J45 SM12J45A	$V_{DRM}$	600		
R.M.S On-State Current (Full Sine Waveform Tc =	I <sub>T (RMS)</sub>	12	А		
Peak One Cycle Surge On-State Current (Non-Repetitive)		I <sub>TSM</sub>	120 (50Hz)	Α	
			132 (60Hz)	^	
I <sup>2</sup> t Limit Value (t = 1~10n	ı <sup>2</sup> t	72	A <sup>2</sup> s		
Critical Rate of Rise of O Current	di / dt	50	A / μs		
Peak Gate Power Dissipa	P <sub>GM</sub>	5	W		
Average Gate Power Dis	P <sub>G (AV)</sub>	0.5	W		
Peak Gate Voltage	$V_{GM}$	10	V		
Peak Gate Current	I <sub>GM</sub>	2	Α		
Junction Temperature	Tj	-40~125	°C		
Storage Temperature Ra	T <sub>stg</sub>	-40~125	°C		



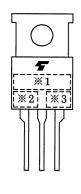
Weight: 2.0g



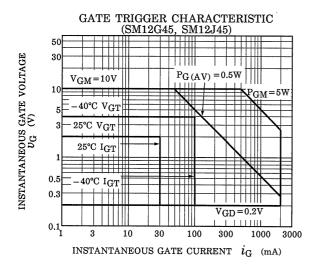
## **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

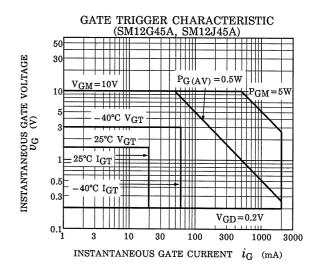
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT		
Repetitive Peak	Off-Sta	ite Current		I <sub>DRM</sub>	V <sub>DRM</sub> =Rated, T <sub>j</sub> = 125°C		_	_	2	mA
Gate Trigger Voltage		SM12G45 SM12J45	I	V <sub>GT</sub>	V <sub>D</sub> = 12V, R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)	_	_	2	V
	SM12		Ш			T2 (+) , Gate (-)	_	_	2	
	SM12		III			T2 (-) , Gate (-)	_	_	2	
			IV			T2 (-) , Gate (+)	_	_	_	
		SM12G45A SM12J45A	I			T2 (+) , Gate (+)	_	_	1.5	
	SM12		II			T2 (+) , Gate (−)	_	_	1.5	
	SM12		III			T2 (-) , Gate (-)	_	_	1.5	
			IV			T2 (-) , Gate (+)	_	_	_	
		SM12G45 SM12J45	I	l <sub>GT</sub>	V <sub>D</sub> = 12V, R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)	_	_	30	- mA
	SM12		II			T2 (+) , Gate (−)	_	_	30	
	SM12		III			T2 (-) , Gate (-)	_	_	30	
			IV			T2 (-) , Gate (+)	_	_	_	
			I			T2 (+) , Gate (+)	_	_	20	
	SM12	2G45A	II			T2 (+) , Gate (−)	_	_	20	
	SM12	SM12J45A	III			T2 (-) , Gate (-)	_	_	20	
						T2 (-) , Gate (+)		_	_	
Peak On-State	Peak On-State Voltage		$V_{TM}$	I <sub>TM</sub> = 17A		_	_	1.5	V	
Gate Non-Trigge	Gate Non-Trigger Voltage		$V_{GD}$	V <sub>D</sub> = Rated, Tc = 125°C		0.2	_	_	V	
Holding Current		I <sub>H</sub>	V <sub>D</sub> = 12V, I <sub>TM</sub> = 1A		_	_	50	mA		
Thermal Resistance		R <sub>th (j-c)</sub>	Junction to Case, AC		_	_	1.8	°C/W		
Critical Rate of Rise of Off-State Voltage at Commutation SM12J4		SM12G45 SM12J45		(dv / dt) c	V <sub>DRM</sub> = 400V				_	V/us
		SM12G45A SM12J45A	-			= - 6.5A / ms		_	_	V/µs

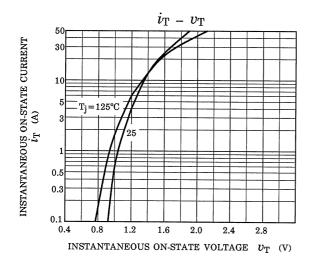
### **MARKING**

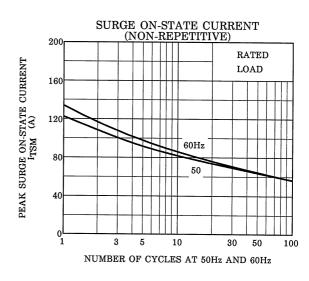


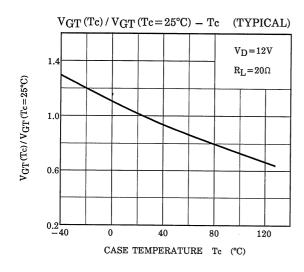
NUMBER	SYMBOL		MARK	
*1		SM12G45, SM12G45A	M12G45	
	TYPE	SM12J45, SM12J45A	M12J45	
*2		SM12G45A, SM12J45A	Α	
*3	Lot Number  Month (Starting from Alphabet A)  Year (Last Decimal Digit of the Current Year)		Example 8A: January 1998 8B: February 1998 8L: December 1998	

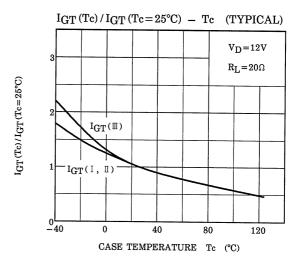


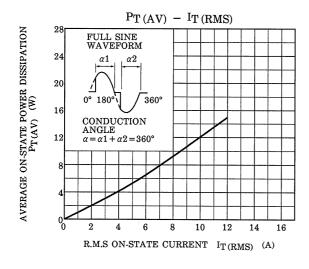


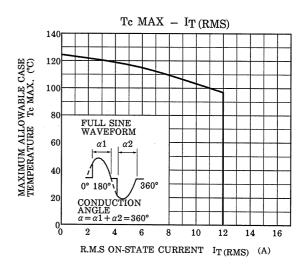


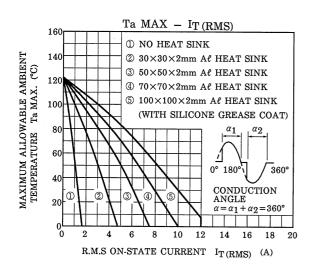


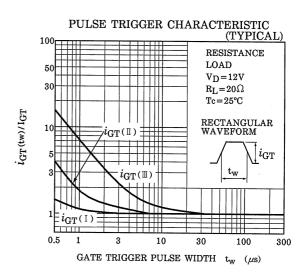


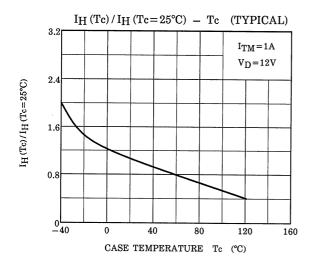


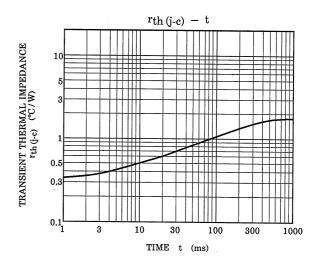












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